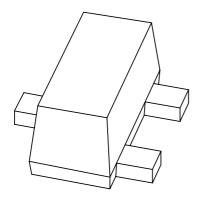
DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS2515F15 V low V_{CEsat} NPN transistor

Product specification Supersedes data of 2001 Jan 26

2001 Sep 21





15 V low V_{CEsat} NPN transistor

PBSS2515F

FEATURES

- · Low collector-emitter saturation voltage
- · High current capabilities
- Improved thermal behaviour due to flat leads.

APPLICATIONS

- · General purpose switching and muting
- · Low frequency driver circuits
- LCD backlighting
- · Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} transistor in a SC-89 (SOT490) plastic package.

PNP complement: PBSS3515F.

MARKING

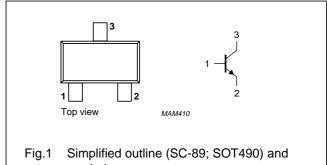
TYPE NUMBER	MARKING CODE		
PBSS2515F	2A		

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	15	V
I _C	collector current (DC)	500	mA
I _{CM}	peak collector current	1	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	15	V
V _{CEO}	collector-emitter voltage	open base	_	15	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	500	mA
I _{CM}	peak collector current		_	1	Α
I _{BM}	peak base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air	500	K/W
	ambient			

CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 15 V; I _E = 0	_	_	100	nA
		V _{CB} = 15 V; I _E = 0; T _j = 150 °C	_	_	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 10 mA	200	_	_	
		$V_{CE} = 2 \text{ V}; I_{C} = 100 \text{ mA}; \text{ note } 1$	150	_	_	
		V _{CE} = 2 V; I _C = 500 mA; note 1	90	_	_	
V _{CEsat}	collector-emitter saturation	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	25	mV
	voltage	$I_C = 200 \text{ mA}; I_B = 10 \text{ mA}$	_	_	150	mV
		$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}; \text{ note 1}$	_	_	250	mV
R _{CEsat}	equivalent on-resistance	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	_	300	<500	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = 500 \text{ mA}$; $I_B = 50 \text{ mA}$; note 1	_	_	1.1	V
V _{BE}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 100 mA; note 1	_	_	0.9	V
f _T	transition frequency	I _C = 100 mA; V _{CE} = 5 V; f = 100 MHz	250	420	_	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	4.4	6	pF

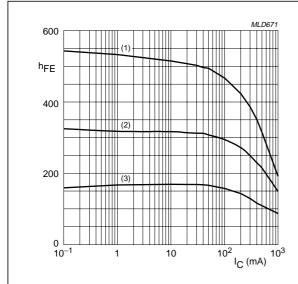
Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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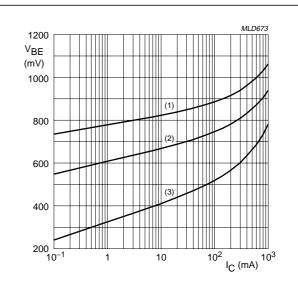
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 $V_{CE} = 2 V.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55$ °C.

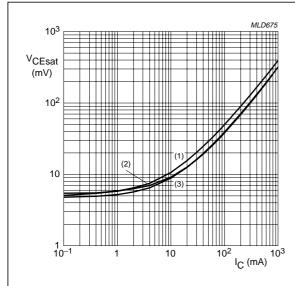
Fig.2 DC current gain as a function of collector current; typical values.



 $V_{CE} = 2 V$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

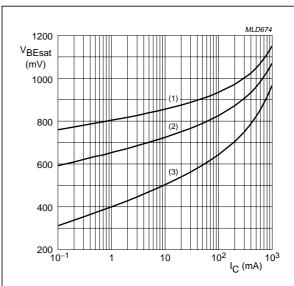
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



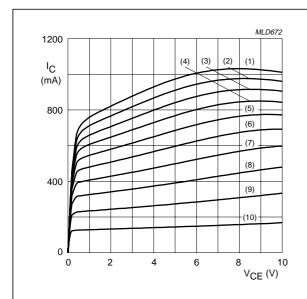
 $I_{\rm C}/I_{\rm B} = 20.$

- (1) $T_{amb} = 150 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \,^{\circ}C$.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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 $T_{amb} = 25 \, ^{\circ}C.$

(1) $I_B = 4.60 \text{ nA}$.

(5) $I_B = 2.76 \text{ nA}.$

(9) $I_B = 0.92 \text{ nA}.$ (10) $I_B = 0.46 \text{ nA}$.

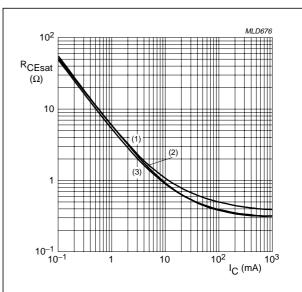
(2) $I_B = 4.14 \text{ nA}.$ (3) $I_B = 3.68 \text{ nA}.$ (6) $I_B = 2.30 \text{ nA}.$

(7) $I_B = 1.84 \text{ nA}.$

(4) $I_B = 3.22 \text{ nA}$.

(8) $I_B = 1.38 \text{ nA}.$

Fig.6 Collector current as a function of collector-emitter voltage; typical values.



 $I_{\rm C}/I_{\rm B} = 20$.

(1) $T_{amb} = 150 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Collector-emitter equivalent on-resistance as a function of collector current; typical values.

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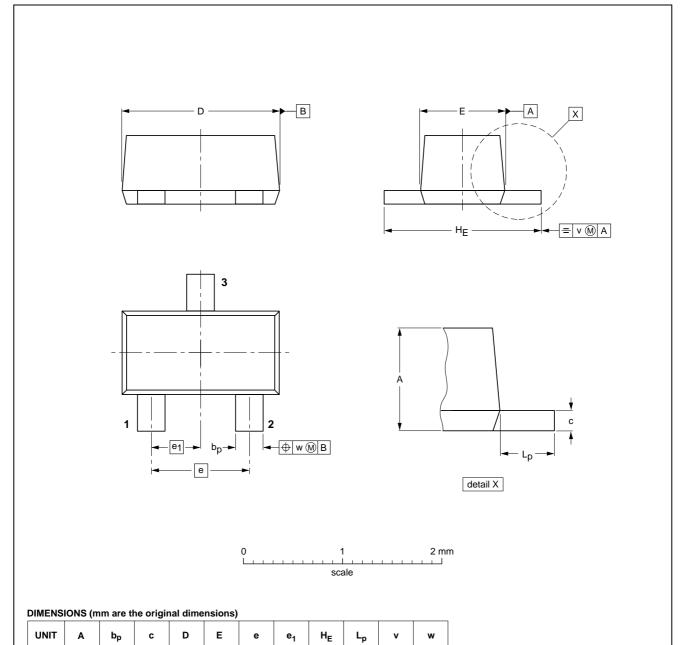
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT490



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DA	
SOT490			SC-89			98-10-23

0.5

0.5 0.3

0.1

0.1

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0.8

mm

0.33 0.23 0.2 0.1

1.7 1.5 0.95 0.75

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